



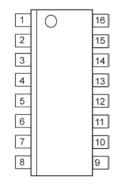
Switching Diode Array Steering Diode TVS Array™

DESCRIPTION

These low capacitance diode arrays are multiple, discrete, isolated junctions fabricated by a planar process and mounted in a 16-Pin SOIC package for use as steering diodes protecting up to eight I/O ports from ESD, EFT, or surge by directing them either to the positive side of the power supply line or to ground (see Figure 1). An external TVS diode may be added between the positive supply line and ground to prevent overvoltage on the supply rail. They may also be used in fast switching core-driver applications. This includes computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, etc., as well as decoding or encoding applications. These arrays offer many advantages of integrated circuits such as high-density packaging and improved reliability. This is a result of fewer pick and place operations, smaller footprint, smaller weight, and elimination of various discrete packages that may not be as user friendly in PC board mounting. They are available with either tin-lead plating terminations or as RoHS compliant with annealed matte-tin finish.



16-Pin Package



Top Viewing Pin Layout

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- 8-diode array protects 8 lines
- Molded 16-Pin SOIC package
- UL 94V-0 flammability classification
- Low capacitance 1.5 pF per diode
- Switching speeds less than 5 ns
- IEC 61000-4 compatible:

61000-4-2 (ESD): Air 15 kV, contact - 8 kV

61000-4-4 (EFT): 40 A - 5/50 ns 61000-4-5 (surge): 12 A, 8/20 µs

RoHS compliant device is available

APPLICATIONS / BENEFITS

- Low capacitance steering diode protection for high frequency data lines

RS-232 & RS-422 Interface Networks.

Ethernet: 10 Base T Computer I/O Ports

LAN

Switching Core Drivers

MSC - Lawrence

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MSC - Ireland

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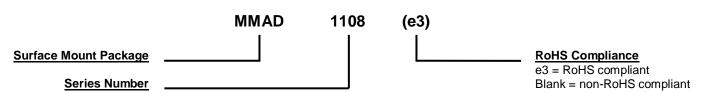
MAXIMUM RATINGS

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-55 to +150	°C/W
Peak Working Reverse Voltage	V_{RWM}	75	V
Repetitive Peak Forward Current (one diode)	I _{FRM}	400	mA
Forward Surge Current @ 8.3 ms	I _{FSM}	2	Α
@ 8/20 μs		12	
Rated Average Power Dissipation (total package)	P _{M(AV)}	1500	mW
Solder Temperature @ 10 s		260	٥C

MECHANICAL and PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy body meeting UL94V-0 flammability classification.
- TERMINALS: Tin-lead or RoHS compliant annealed matte-tin plating solderable per MIL-STD-750 method 2026.
- MARKING: MSC logo, MMAD1108 or MMAD1108e3 and date code. Pin #1 is to the left of the dot or indent on top of package.
- DELIVERY option: Tape and reel or carrier tube. Consult factory for quantities.
- WEIGHT: Approximately 0.127 grams
- See Package Dimensions on last page.

PART NOMENCLATURE



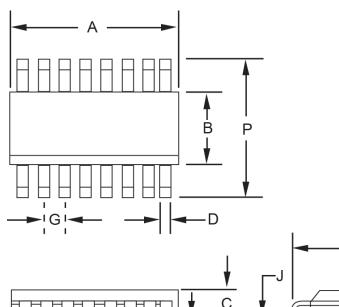
SYMBOLS & DEFINITIONS				
Symbol	Definition			
Ст	Total Capacitance: The total small signal capacitance between the diode terminals of a complete device.			
I_R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.			
V _(BR)	Breakdown Voltage: The voltage across the device at a specified current I _(BR) in the breakdown region.			
V_{F}	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.			
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.			

ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise stated

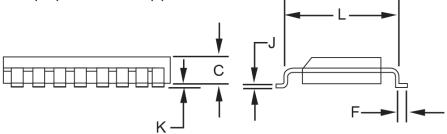
PART NUMBER	BREAKDOWN VOLTAGE V _(BR) @ I _(BR) =100 μA	LEAK CURF I _I T _A = 2	RENT	LEAK CURI I T _A = 1	RENT	TOTAL CAPACITANCE C _T @ 0 V	REVERSE RECOVERY TIME t _{rr}	FORWARD VOLTAGE V _F I _F = 10 mA	FORWARD VOLTAGE V _F I _F = 100 mA
	V	μ	A	μ	Α	pF	ns	V	V
	MIN	MAX	@ V _R	MAX	$@V_R$	TYP	MAX	MAX	MAX
MMAD1108 MMAD1108e3	90	0.200	20	300	20	1.5	5.0	1.00	1.20



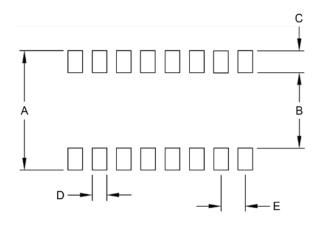
PACKAGE DIMENSIONS



	Dimensions						
Ref.	Ir	nch	Millimeters				
	Min Max		Min	Max			
Α	0.358	0.398	9.09	10.10			
В	0.150	0.158	3.81	4.01			
С	0.053	0.069	1.35	1.75			
D	0.011	0.021	0.28	0.53			
F	0.016	0.050	0.41	1.27			
G	0.050) BSC	1.27 BSC				
J	0.006	0.010	0.15	0.25			
K	0.004	0.008	0.10	0.20			
L	0.189	0.206	4.80	5.23			
Р	0.228	0.244	5.79	6.19			

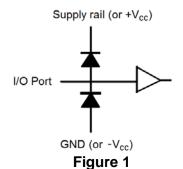


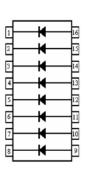
PAD LAYOUT



	Dimensions				
Ref.	Inch	Millimeters			
	Typical	Typical			
Α	0.275	7.0			
В	0.155	4.0			
С	0.060	1.52			
D	0.024	0.6			
E	0.050	1.270			

SCHEMATIC AND CIRCUIT





Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microsemi:

MMAD1108e3/TR13 MMAD1108/TR13